

# BLD6G22L-50; BLD6G22LS-50

W-CDMA 2110 MHz to 2170 MHz fully integrated Doherty transistor

Rev. 3 — 17 August 2010

Product data sheet

## 1. Product profile

### 1.1 General description

The BLD6G22L-50 and BLD22LS-50 incorporate a fully integrated Doherty solution using NXP's state of the art GEN6 LDMOS technology. This device is perfectly suited for CDMA base station applications at frequencies from 2110 MHz to 2170 MHz. The main and peak device, input splitter and output combiner are integrated in a single package. This package consists of one gate and drain lead and two extra leads of which one is used for biasing the peak amplifier and the other is not connected. It only requires the proper input/output match and bias setting as with a normal class-AB transistor.

**Table 1. Typical performance**

RF performance at  $T_h = 25^\circ\text{C}$ .

Mode of operation	f (MHz)	$V_{DS}$ (V)	$P_{L(AV)}$ (W)	$G_p$ (dB)	$\eta_D$ (%)	ACPR (dBc)	$P_{L(3dB)}$ (W)
W-CDMA [1][2]	2110 to 2170	28	8	14	40	-30	55

[1] Test signal: 2-carrier W-CDMA; test model 1; 64 DPCH; PAR = 8.3 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz.

[2]  $I_{Dq} = 170 \text{ mA}$  (main);  $V_{GS(\text{amp})\text{peak}} = 0 \text{ V}$ .

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features and benefits

- Typical W-CDMA performance at frequencies from 2110 MHz to 2170 MHz:
  - ◆ Average output power = 8 W
  - ◆ Power gain = 14 dB
  - ◆ Efficiency = 40 %
- Fully optimized integrated Doherty concept:
  - ◆ integrated asymmetrical power splitter at input
  - ◆ integrated power combiner
  - ◆ peak biasing down to 0 V
  - ◆ low junction temperature
  - ◆ high efficiency



- 100 % peak power tested for guaranteed output power capability
- Integrated ESD protection
- Good pair match (main and peak on the same chip)
- Independent control of main and peak bias
- Internally matched for ease of use
- Excellent ruggedness
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- High efficiency RF power amplifiers with digital pre-distortion for W-CDMA multi carrier applications in the 2110 MHz to 2170 MHz range.

## 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
<b>BLD6G22L-50 (SOT1130A)</b>			
1	drain		
2	gate + bias main		
3	source	[1]	
4	n.c.		
5	bias peak		
<b>BLD6G22LS-50 (SOT1130B)</b>			
1	drain		
2	gate + bias main		
3	source	[1]	
4	n.c.		
5	bias peak		

[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BLD6G22L-50	-	flanged ceramic package; 2 mounting holes; 4 leads	SOT1130A
BLD6G22LS-50	-	earless flanged ceramic package; 4 leads	SOT1130B

## 4. Block diagram

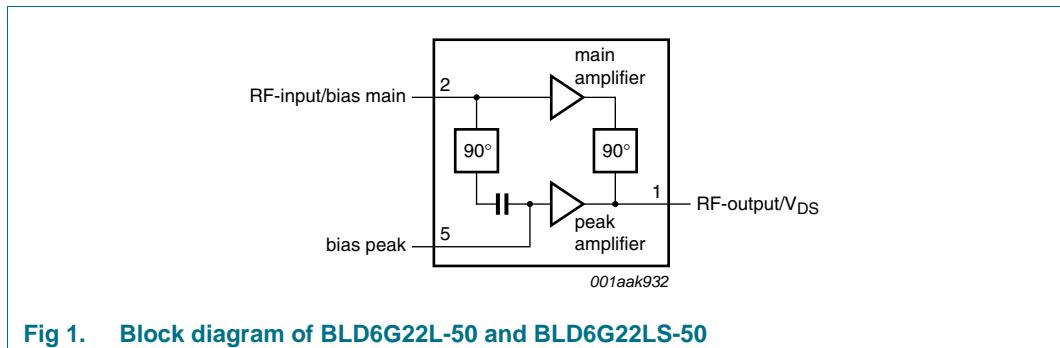


Fig 1. Block diagram of BLD6G22L-50 and BLD6G22LS-50

## 5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).  
Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS(\text{amp})\text{main}}$	main amplifier gate-source voltage		-0.5	+13	V
$V_{GS(\text{amp})\text{peak}}$	peak amplifier gate-source voltage		-0.5	+13	V
$I_D$	drain current		-	10.2	A
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	200	°C

## 6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j\text{-case})}$	thermal resistance from junction to case	$T_{case} = 80$ °C; $P_L = 8$ W	[1] 1.9	K/W

[1] When operated with a 2-carrier (W-CDMA) modulated signal with PAR = 8.3 dB at 0.01 % probability on the CCDF.

## 7. Characteristics

Table 6. Characteristics

Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$ V; $I_D = 0.62$ mA	65	-	-	V
$V_{GS(\text{th})}$	gate-source threshold voltage	$V_{DS} = 10$ V; $I_D = 31$ mA	1.4	1.8	2.4	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 28$ V; $I_D = 170$ mA	1.55	2.05	2.55	V
$I_{DSS}$	drain leakage current	$V_{GS} = 0$ V; $V_{DS} = 28$ V	-	-	1.4	μA
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(\text{th})} + 3.75$ V; $V_{DS} = 10$ V	4.95	5.5	-	A

**Table 6. Characteristics ...continued**  
Valid for both main and peak device.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{GSS}$	gate leakage current	$V_{GS} = 11$ V; $V_{DS} = 0$ V	-	-	140	nA
$g_{fs}$	forward transconductance	$V_{DS} = 10$ V; $I_D = 1.55$ A	1.4	2.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75$ V; $I_D = 1.085$ A	-	0.52	0.736	$\Omega$

## 8. Application information

**Table 7. Application information**

Mode of operation: 2-carrier W-CDMA; PAR 8.3 dB at 0.01 % probability on CCDF; carrier spacing = 5 MHz;  $f = 2140$  MHz; RF performance at  $V_{DS} = 28$  V;  $I_{Dq} = 170$  mA;  $V_{GS(amp)peak} = 0$  V;  $T_{case} = 25$  °C; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	8	-	W
$G_p$	power gain	$P_{L(AV)} = 8$ W	12.5	14	-	dB
$\eta_D$	drain efficiency	$P_{L(AV)} = 8$ W	37	40	-	%
$PAR_O$	output peak-to-average ratio	$P_{L(AV)} = 8$ W	-	7.6	-	dB
$RL_{in}$	input return loss	$P_{L(AV)} = 8$ W	10	17	-	dB
ACPR	adjacent channel power ratio	$P_{L(AV)} = 8$ W	-	-30	-24	dBc

**Table 8. Application information**

Mode of operation: Pulsed CW;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s; RF performance at  $V_{DS} = 28$  V;  $I_{Dq} = 170$  mA;  $V_{GS(amp)peak} = 0$  V;  $T_{case} = 25$  °C; unless otherwise specified; in a production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(3dB)}$	output power at 3 dB gain compression		46	55	-	W

### 8.1 Ruggedness in Doherty operation

The BLD6G22L-50 and BLD6G22LS-50 are capable of withstanding a load mismatch corresponding to  $VSWR = 10 : 1$  through all phases under the following conditions:  $V_{DS} = 28$  V;  $I_{Dq} = 170$  mA;  $P_L = 8$  W (W-CDMA);  $f = 2140$  MHz.

### 8.2 Impedance information

**Table 9. Typical impedance**

Measured load-pull data; typical values unless otherwise specified.

$f$ MHz	$Z_S$ $\Omega$	$Z_L$ $\Omega$
2050	9.4 – 12.3j	5.5 – 7.6j
2110	11.4 – 11.2j	6.7 – 8.2j
2140	12.3 – 10.5j	7.0 – 7.5j
2170	12.2 – 9.3j	7.2 – 6.8j
2230	11.8 – 7.3j	5.4 – 5.5j

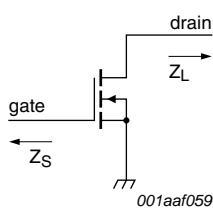
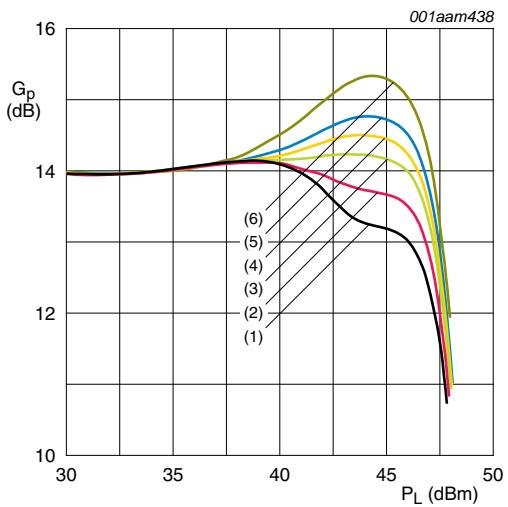


Fig 2. Definition of transistor impedance

### 8.3 Performance curves

Performance curves are measured in a BLD6G22L-50 application circuit.

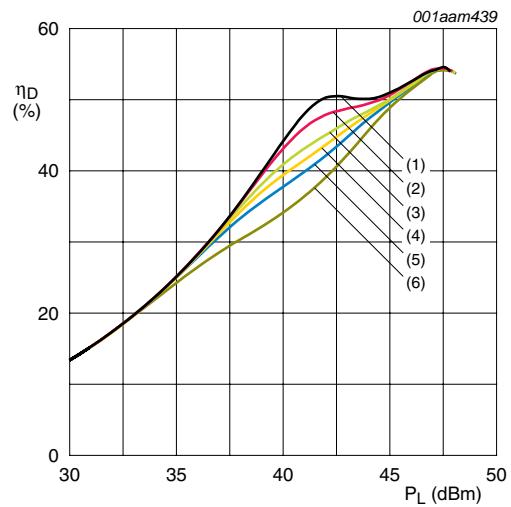
#### 8.3.1 CW pulsed



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $f = 2140$  MHz;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s on 1 ms period.

- (1)  $V_{GS(\text{amp})\text{peak}} = 0$  V
- (2)  $V_{GS(\text{amp})\text{peak}} = 0.2$  V
- (3)  $V_{GS(\text{amp})\text{peak}} = 0.4$  V
- (4)  $V_{GS(\text{amp})\text{peak}} = 0.5$  V
- (5)  $V_{GS(\text{amp})\text{peak}} = 0.6$  V
- (6)  $V_{GS(\text{amp})\text{peak}} = 0.8$  V

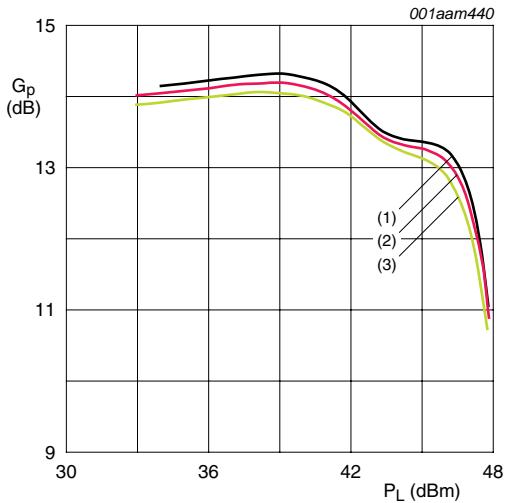
Fig 3. Power gain as a function of load power; typical values



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $f = 2140$  MHz;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s on 1 ms period.

- (1)  $V_{GS(\text{amp})\text{peak}} = 0$  V
- (2)  $V_{GS(\text{amp})\text{peak}} = 0.2$  V
- (3)  $V_{GS(\text{amp})\text{peak}} = 0.4$  V
- (4)  $V_{GS(\text{amp})\text{peak}} = 0.5$  V
- (5)  $V_{GS(\text{amp})\text{peak}} = 0.6$  V
- (6)  $V_{GS(\text{amp})\text{peak}} = 0.8$  V

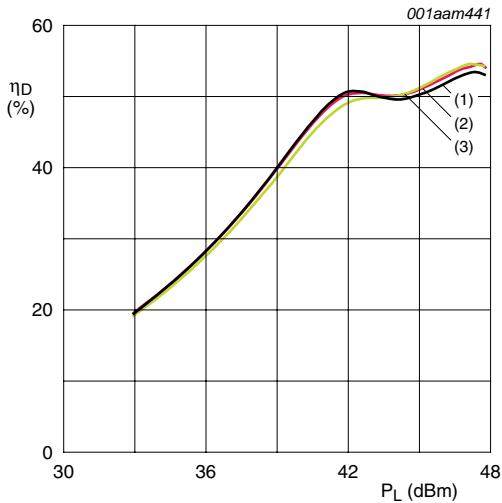
Fig 4. Drain efficiency as a function of load power; typical values



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $V_{GS(amp)peak} = 0$  V;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s on 1 ms period.

(1)  $f = 2110$  MHz  
(2)  $f = 2140$  MHz  
(3)  $f = 2170$  MHz

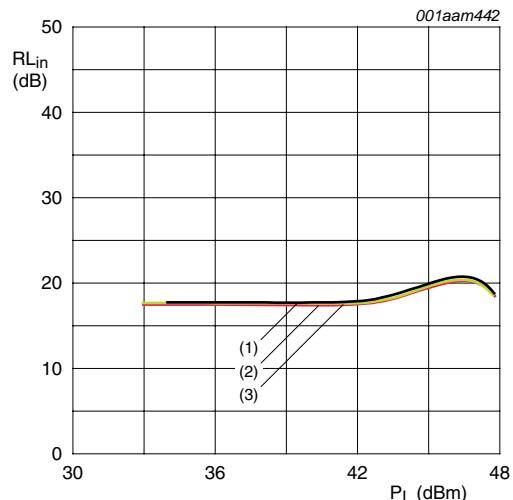
**Fig 5. Power gain as a function of load power; typical values**



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $V_{GS(amp)peak} = 0$  V;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s on 1 ms period.

(1)  $f = 2110$  MHz  
(2)  $f = 2140$  MHz  
(3)  $f = 2170$  MHz

**Fig 6. Drain efficiency as a function of load power; typical values**

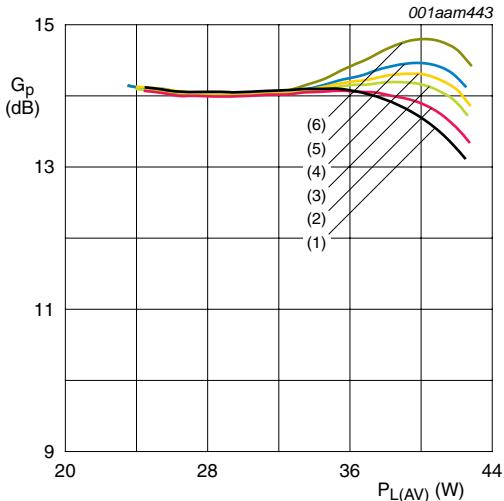


$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  $V_{GS(amp)peak} = 0$  V;  $\delta = 10$  %;  $t_p = 100$   $\mu$ s on 1 ms period.

(1)  $f = 2110$  MHz  
(2)  $f = 2140$  MHz  
(3)  $f = 2170$  MHz

**Fig 7. Input return loss as a function of load power; typical values**

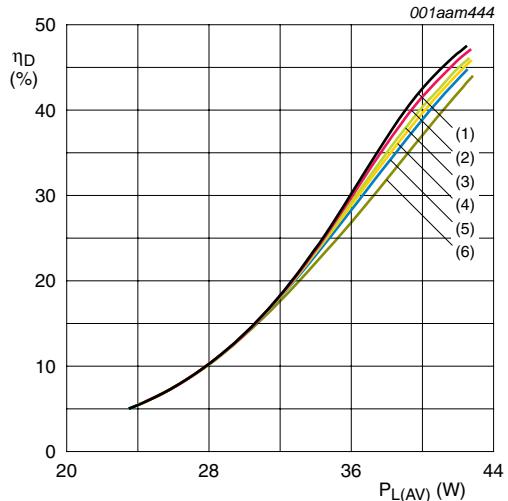
## 8.3.2 W-CDMA



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  $f = 2140$  MHz; 2-carrier W-CDMA; PAR = 8.3 dB at 0.01 % probability on CCDF.

- (1)  $V_{GS(\text{amp})\text{peak}} = 0$  V
- (2)  $V_{GS(\text{amp})\text{peak}} = 0.2$  V
- (3)  $V_{GS(\text{amp})\text{peak}} = 0.4$  V
- (4)  $V_{GS(\text{amp})\text{peak}} = 0.5$  V
- (5)  $V_{GS(\text{amp})\text{peak}} = 0.6$  V
- (6)  $V_{GS(\text{amp})\text{peak}} = 0.8$  V

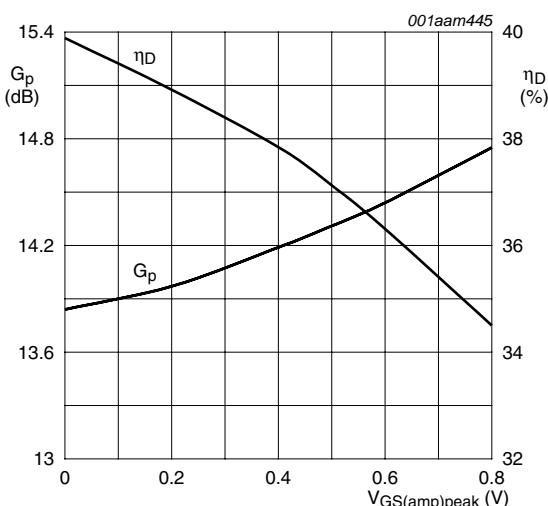
**Fig 8. Power gain as a function of average load power; typical values**



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  $f = 2140$  MHz; 2-carrier W-CDMA; PAR = 8.3 dB at 0.01 % probability on CCDF.

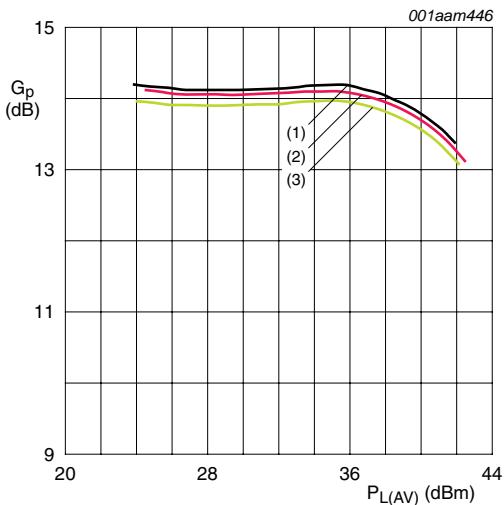
- (1)  $V_{GS(\text{amp})\text{peak}} = 0$  V
- (2)  $V_{GS(\text{amp})\text{peak}} = 0.2$  V
- (3)  $V_{GS(\text{amp})\text{peak}} = 0.4$  V
- (4)  $V_{GS(\text{amp})\text{peak}} = 0.5$  V
- (5)  $V_{GS(\text{amp})\text{peak}} = 0.6$  V
- (6)  $V_{GS(\text{amp})\text{peak}} = 0.8$  V

**Fig 9. Drain efficiency as a function of average load power; typical values**



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  $f = 2140$  MHz; 2-carrier W-CDMA; PAR = 8.3 dB at 0.01 % probability on CCDF.

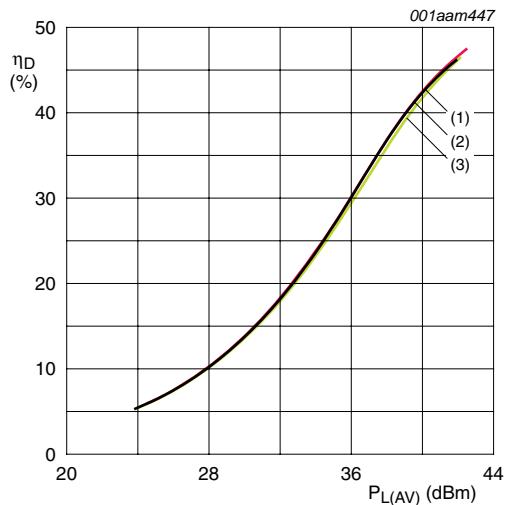
**Fig 10. Power gain and drain efficiency as function of load power; typical values**



$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $V_{GS(amp)peak} = 0$  V; 2-carrier W-CDMA; PAR = 8.3 dB at  
0.01 % probability on CCDF.

- (1)  $f = 2110$  MHz
- (2)  $f = 2140$  MHz
- (3)  $f = 2170$  MHz

**Fig 11. Power gain as a function of average load power; typical values**

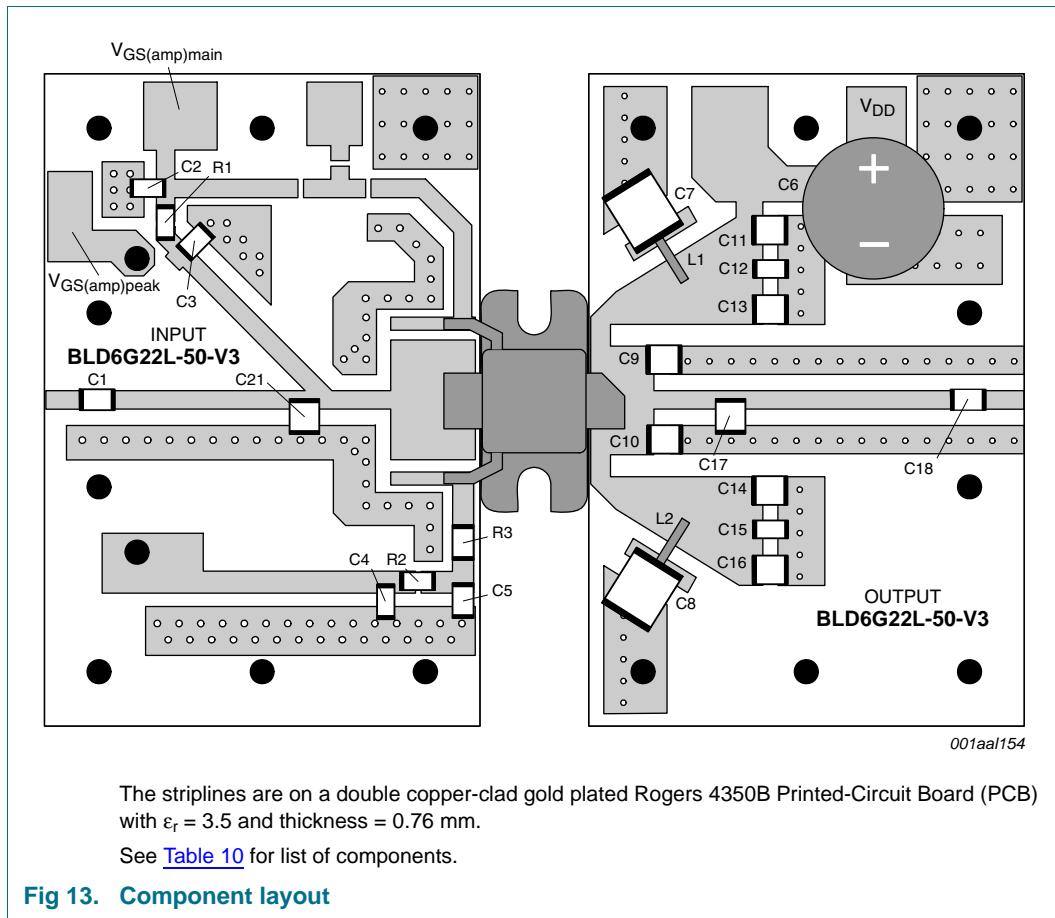


$V_{DS} = 28$  V;  $I_{DQ} = 170$  mA (main);  $T_{case} = 25$  °C;  
 $V_{GS(amp)peak} = 0$  V; 2-carrier W-CDMA; PAR = 8.3 dB at  
0.01 % probability on CCDF.

- (1)  $f = 2110$  MHz
- (2)  $f = 2140$  MHz
- (3)  $f = 2170$  MHz

**Fig 12. Drain efficiency as a function of average load power; typical values**

## 9. Test information



**Fig 13. Component layout**

**Table 10. List of components**

See [Figure 13](#) for component layout.

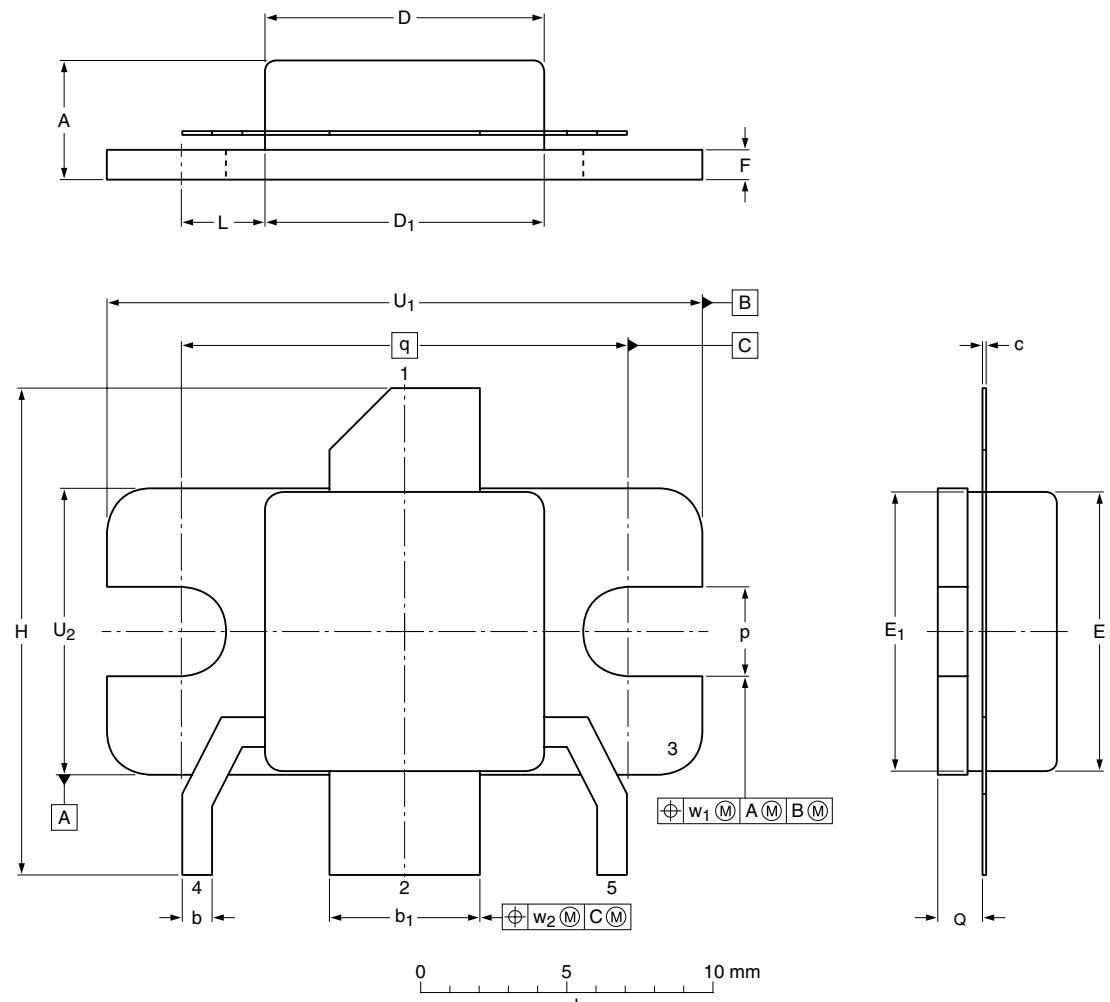
Component	Description	Value	Dimensions
C1, C3, C5, C18	multilayer ceramic chip capacitor	9.1 pF	<a href="#">[1]</a>
C2, C4, C12, C15	multilayer ceramic chip capacitor	100 nF	
C6	electrolytic capacitor	470 $\mu$ F; 63 V	
C7, C8	multilayer ceramic chip capacitor	10 $\mu$ F	
C9, C10	multilayer ceramic chip capacitor	1.2 pF	<a href="#">[1]</a>
C11, C13, C14, C16	multilayer ceramic chip capacitor	8.2 pF	<a href="#">[1]</a>
C17	multilayer ceramic chip capacitor	0.8 pF	<a href="#">[1]</a>
C21	multilayer ceramic chip capacitor	1.0 pF	<a href="#">[1]</a>
L1, L2	copper wire	-	diameter = 0.8 mm; length = 8 mm
R1	SMD resistor	3.6 $\Omega$	1206
R2	SMD resistor	33 $\Omega$	1206
R3	SMD resistor	10 $\Omega$	1206

[1] American Technical Ceramics type 100B or capacitor of same quality.

## 10. Package outline

Flanged ceramic package; 2 mounting holes; 4 leads

SOT1130A



### Dimensions

Unit <sup>(1)</sup>	A	b	b <sub>1</sub>	c	D	D <sub>1</sub>	E	E <sub>1</sub>	F	H	L	p	Q <sup>(2)</sup>	q	U <sub>1</sub>	U <sub>2</sub>	w <sub>1</sub>	w <sub>2</sub>
mm max	4.65	1.14	5.26	0.18	9.65	9.65	9.65	9.65	1.14	17.12	3.00	3.30	1.70		20.45	9.91		
mm nom	3.76	0.89	5.00	0.10	9.40	9.40	9.40	9.40	0.89	16.10	2.69	2.92	1.45	15.24		0.25	0.51	
mm min	3.76	0.89	5.00	0.10	9.40	9.40	9.40	9.40	0.89	16.10	2.69	2.92	1.45		20.19	9.65		
inches max	0.183	0.045	0.207	0.007	0.38	0.38	0.38	0.38	0.045	0.674	0.118	0.130	0.067		0.805	0.39		
inches nom	0.148	0.035	0.197	0.004	0.37	0.37	0.37	0.37	0.035	0.634	0.106	0.115	0.057	0.6		0.01	0.02	
inches min	0.148	0.035	0.197	0.004	0.37	0.37	0.37	0.37	0.035	0.634	0.106	0.115	0.057	0.795	0.38			

### Note

1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

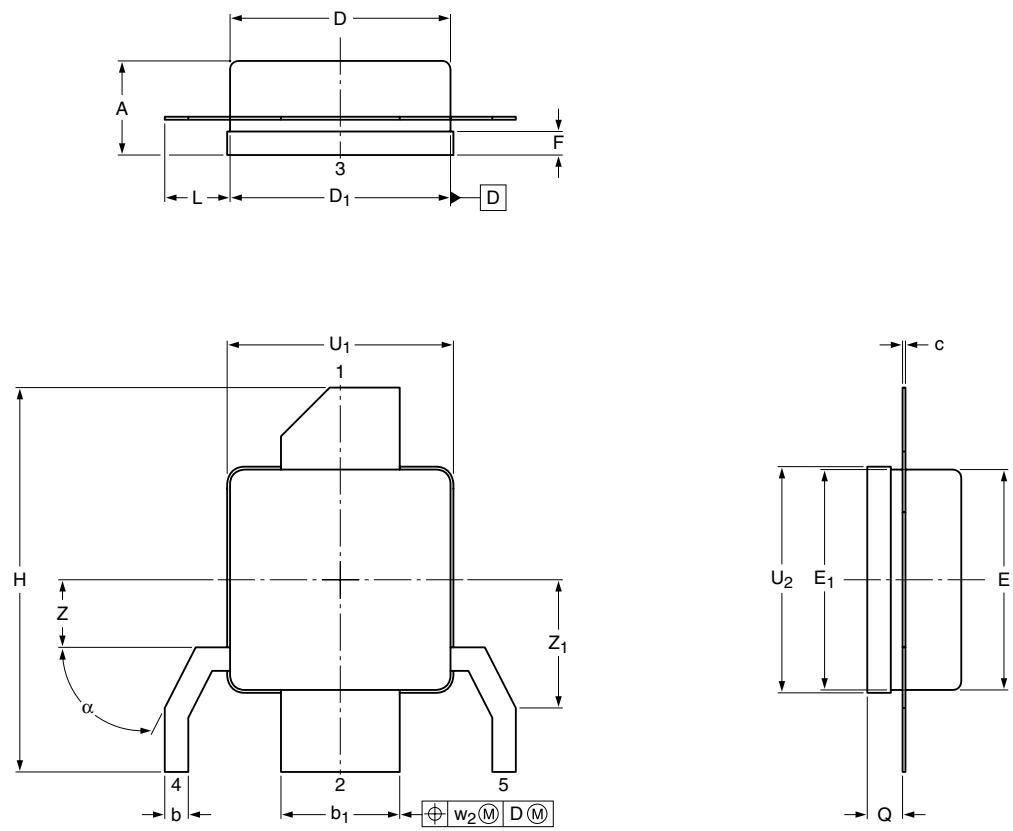
sot1130a\_p0

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT1130A					09-10-12- 10-02-02

Fig 14. Package outline SOT1130A

## Earless flanged ceramic package; 4 leads

SOT1130B



## Dimensions

Unit <sup>(1)</sup>	A	b	b <sub>1</sub>	c	D	D <sub>1</sub>	E	E <sub>1</sub>	F	H	L	Q	U <sub>1</sub>	U <sub>2</sub>	w <sub>2</sub>	Z	Z <sub>1</sub>	α
mm max	4.65	1.14	5.26	0.18	9.65	9.65	9.65	9.65	1.14	17.12	3.00	1.70	9.91	9.91	3.05	5.66	64°	
mm nom	3.76	0.89	5.00	0.10	9.40	9.40	9.40	9.40	0.89	16.10	2.69	1.45	9.65	9.65	0.51	2.79	5.41	62°
mm min	3.76	0.89	5.00	0.10	9.40	9.40	9.40	9.40	0.89	16.10	2.69	1.45	9.65	9.65	3.05	5.66	64°	
inches nom	0.183	0.045	0.207	0.007	0.38	0.38	0.38	0.38	0.045	0.674	0.118	0.069	0.39	0.39	0.120	0.223	64°	
inches min	0.148	0.035	0.197	0.004	0.37	0.37	0.37	0.37	0.035	0.634	0.106	0.059	0.38	0.38	0.110	0.213	62°	

## Note

1. millimeter dimensions are derived from the original inch dimensions.
2. dimension is measured 0.030 inch (0.76 mm) from the body.

sot1130b\_po

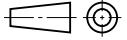
Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT1130B					-09-10-12-09-12-14

Fig 15. Package outline SOT1130B

## 11. Abbreviations

**Table 11. Abbreviations**

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CDMA	Code Division Multiple Access
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
PAR	Peak-to-Average power Ratio
RF	Radio Frequency
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 12. Revision history

**Table 12. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLD6G22L-50_BLD6G22LS-50 v.3	20100817	Product data sheet	-	BLD6G22L-50_BLD6G22LS-50 v.2
Modifications:	<ul style="list-style-type: none"> <li>• <a href="#">Table 1 on page 1</a>: The value of <math>\eta_D</math> has been changed.</li> <li>• <a href="#">Table 6 on page 3</a>: The values of <math>I_{DSX}</math> have been changed.</li> <li>• <a href="#">Table 7 on page 4</a>: Several values have been changed or added.</li> <li>• <a href="#">Table 8 on page 4</a>: Table has been added.</li> <li>• <a href="#">Section 8.3 on page 5</a>: Figures have been updated.</li> </ul>			
BLD6G22L-50_BLD6G22LS-50 v.2	20100318	Objective data sheet	-	BLD6G22L-50_BLD6G22LS-50 v.1
BLD6G22L-50_BLD6G22LS-50 v.1	20091215	Objective data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 13.2 Definitions

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